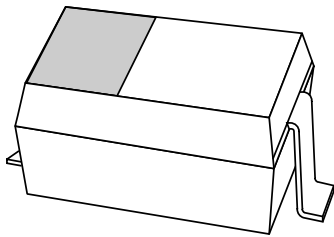


DATA SHEET



PMEG1020EA

Ultra low V_F MEGA Schottky barrier diode

Preliminary specification

2003 Mar 07

Ultra low V_F MEGA Schottky barrier diode

PMEG1020EA

FEATURES

- Forward current: 2 A
- Reverse voltage: 10 V
- Ultra low forward voltage
- Very small plastic SMD package.

APPLICATIONS

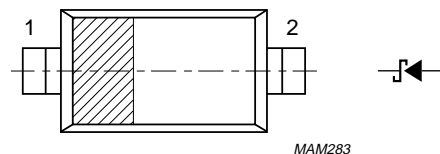
- Low voltage rectification
- High efficiency DC/DC conversion
- Switch mode power supply
- Inverse polarity protection
- Low power consumption applications.

DESCRIPTION

Planar Maximum Efficiency General Application (MEGA) Schottky barrier diode with an integrated guard ring for stress protection, encapsulated in a SOD323 (SC-76) very small SMD plastic package.

PINNING

PIN	DESCRIPTION
1	cathode
2	anode



MAM283

Marking code: E2.

The marking bar indicates the cathode.

Fig.1 Simplified outline (SOD323; SC-76) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_R	continuous reverse voltage		–	10	V
I_F	continuous forward current	$T_{sp} \leq 55\text{ °C}$	–	2	A
I_{FRM}	repetitive peak forward current	$t_p \leq 1\text{ ms}; \delta \leq 0.5$	–	3.2	A
I_{FSM}	non-repetitive peak forward current	$t_p = 8\text{ ms square wave}$	–	9	A
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

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ELECTRICAL CHARACTERISTICS $T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_F	forward voltage	see Fig.2; note 1			
		$I_F = 0.01\text{ A}$	100	130	mV
		$I_F = 0.1\text{ A}$	170	200	mV
		$I_F = 1\text{ A}$	280	350	mV
		$I_F = 2\text{ A}$	350	460	mV
I_R	reverse current	see Fig.3; note 2			
		$V_R = 5\text{ V}$	0.7	2	mA
		$V_R = 8\text{ V}$	1	2.5	mA
		$V_R = 10\text{ V}$	1.2	3	mA
C_d	diode capacitance	$V_R = 5\text{ V}$; $f = 1\text{ MHz}$; see Fig.4	37	45	pF

Notes

1. Pulse test: $t_p = 300\text{ }\mu\text{s}$; $\delta = 0.02$.
2. For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses (P_R) are a significant part of the total power losses.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	450	K/W
		note 2	210	K/W
$R_{th\ j-s}$	thermal resistance from junction to solder point	note 3	90	K/W

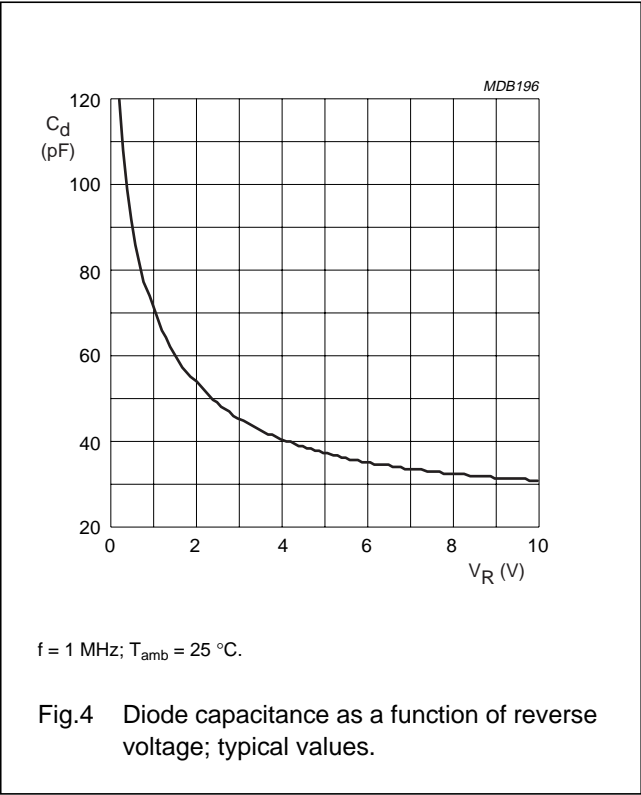
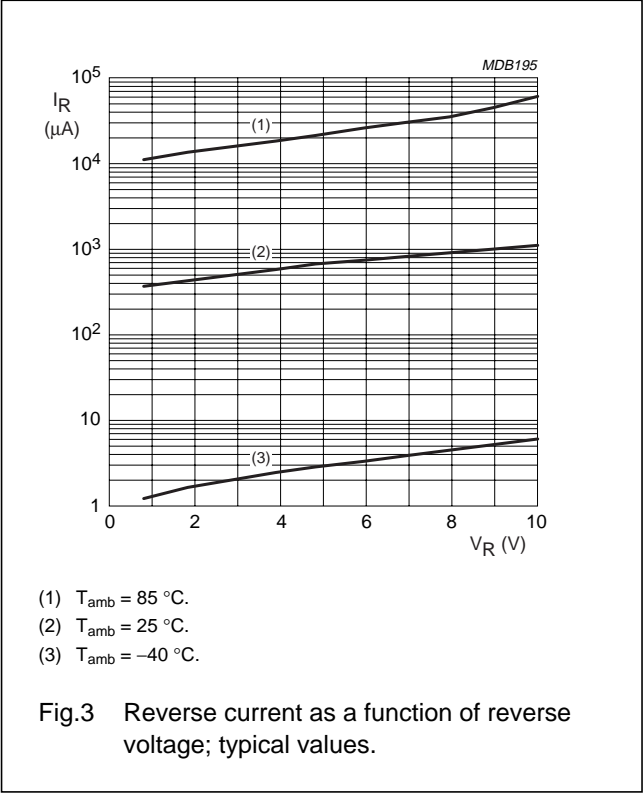
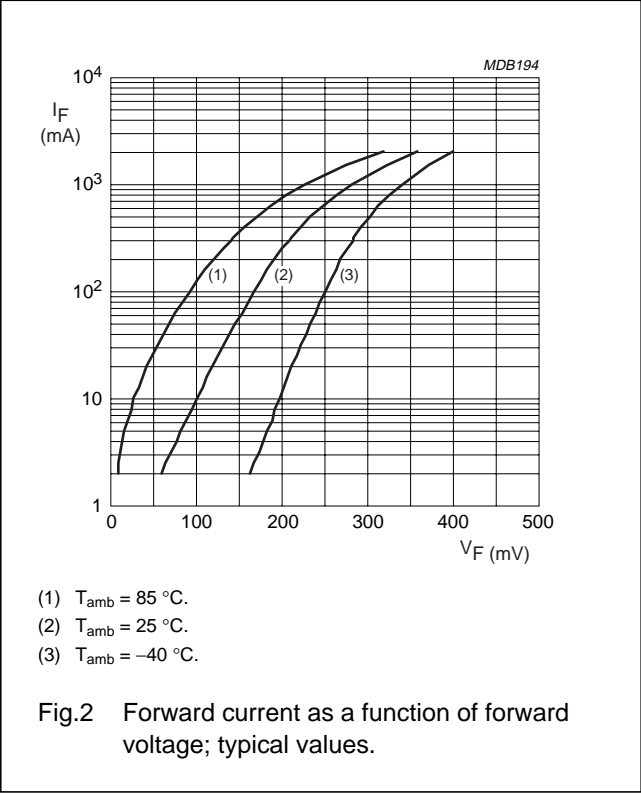
Notes

1. Refer to SOD323 (SC-76) standard mounting conditions.
2. Device mounted on an FR4 printed-circuit board with copper clad 10 x 10 mm.
3. Solder point of cathode tab.

Ultra low V_F MEGA Schottky barrier diode

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GRAPHICAL DATA



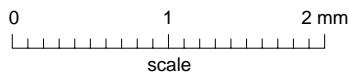
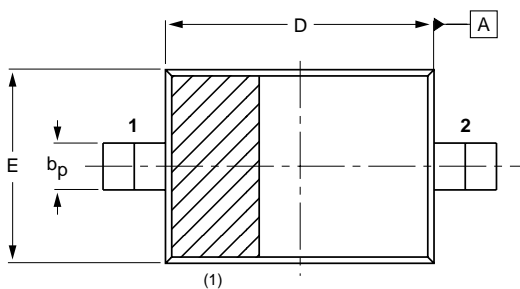
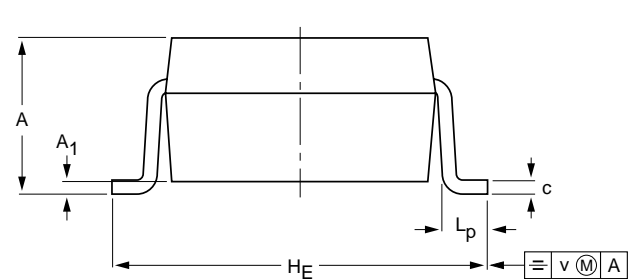
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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A1 max.	bp	c	D	E	HE	LP	Q	v
mm	1.1 0.8	+ 0.05 - 0.05	0.40 0.25	0.25 0.10	1.8 1.6	1.35 1.15	2.7 2.3	0.45 0.15	0.25 0.15	0.2

Note

1. The marking bar indicates the cathode.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOD323			SC-76			98-09-14 99-09-13

Ultra low V_F MEGA Schottky barrier diode

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DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

Notes

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2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.
3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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